

2. (Canceled)

3. (Canceled)

*Cond.
B1*
4. (Amended) The wafer carrier of claim 1, having one of the first wafer and the second wafer in the recess.

5. (Amended) The wafer carrier of claim 4, wherein each of the first wafer, the second wafer, and the recess has a cylindrical shape.

6. (Amended) The wafer carrier of claim 5, wherein one of the first wafer and the second wafer has an outer diameter of about 100 mm.

7. (Canceled)

8. (Amended) The wafer carrier of claim 5, wherein one of the first wafer and the second wafer has an outer diameter of about 150 mm.

9. (Amended) The wafer carrier of claim 5, wherein one of the first wafer and the second wafer has an outer diameter of about 125 mm.

10. The wafer carrier of claim 1, having a generally planar body.

11. The wafer carrier of claim 1, having a circular shape.

12. The wafer carrier of claim 1, wherein the recess is defined by a flat floor to accommodate a flat surface of one of the first wafer and the second wafer.

13. (Canceled)

14. (Amended) The wafer carrier of claim 1, formed of a semiconductor wafer material.

15. The wafer carrier of claim 1, formed of a material selected from the group consisting of silicon carbide, silicon, quartz, graphite, boron nitride, aluminum oxide, aluminum nitride, silicon carbide on graphite, titanium carbide on graphite, glassy carbon, sapphire, indium phosphide, gallium antimonide, gallium arsenide and III-V nitrides.

16. (Amended) The wafer carrier of claim 1 formed of a material of one of the first wafer and the second wafer.

17. (Amended) The wafer carrier of claim 16, wherein the material is selected from the group consisting of silicon carbide, silicon, quartz, graphite, boron nitride, aluminum oxide, aluminum nitride, titanium carbide, glassy carbon,

sapphire, indium phosphide, gallium antimonide, gallium arsenide and III-V nitrides.

*cancel
B1*
18. (Amended) The wafer carrier of claim 1, wherein the wafer carrier is formed of a different material than that of one of the first wafer and the second wafer.

19. (Amended) The wafer carrier of claim 18 formed of a material that is more etch-resistant than a material of one of the first wafer and the second wafer.

20. - 70. (Canceled)